

FEATURES

- 1). Interdigitated amplifying gates
- 2). Fast turn-on and high di/dt
- 3). Low switching losses

$I_{T(AV)}$	2749A
V_{DRM}/V_{RRM}	800~1800V
t_q	35~60 μ s
I_{TSM}	35.6KA
I^2t	6337 $10^3 A^2s$

TYPICAL APPLICATIONS

- 1). Inductive heating
- 2). Electronic welders
- 3). Self-commutated inverters



THE MAIN PARAMETERS

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled, $T_{hs}=55^{\circ}C$	125			2749	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V_{DRM} & V_{RRM} , $t_p=10ms$ V_{DSM} & $V_{RSM} = V_{DRM}$ & $V_{RRM} + 100V$	125	800		1800	V
I_{DRM} I_{RRM}	Repetitive peak off-state current Repetitive peak reverse current	$V_D = V_{DRM}$ $V_R = V_{RRM}$	125			200	mA
I_{TSM} I^2t	Surge on-state current I^2T for fusing coordination	10ms half sine wave $V_R=0.6V_{RRM}$	125			35.6 6337	KA $A^2s \cdot 10^3$
V_{TO}	Threshold voltage		125			1.30	V
r_T	On-state slop resistance		125			0.15	$m\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=4000A$, $F=40KN$	125			1.90	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			500	$V/\mu s$
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 3000A, Gate pulse $t_r \leq 0.5 \mu s$ $I_{GM}=1.5A$	125			1200	$A/\mu s$
I_m	Reverse recovery current	$I_{TM}=2000A$, $t_p=1000 \mu s$, $di/dt=-20A/\mu s$, $VR=50V$	125			178	A
t_{rr}	Reverse recovery time					10.5	μs
Q_{rr}	Recovery charge					934	1100
t_q	Circuit commutated turn-off time	$I_{TM}=2000A$, $t_p=1000 \mu s$, $V_R=50V$ $dv/dt=30V/\mu s$, $di/dt=-20A/\mu s$	125	35		60	μs
I_{GT}	Gate trigger current	$V_A=12V$, $I_A=1A$	25	40		450	mA
V_{GT}	Gate trigger voltage			0.9		4.5	V
I_H	Holding current			20		1000	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.3			V
$R_{th(j-h)}$	Thermal resistance Junction to heatsink	At 180° sine, double side cooled Clamping force 40KN				0.011	$^{\circ}C/W$
F_m	Mounting force			35		47	KN
T_{stg}	Stored temperature			-40		140	$^{\circ}C$
W_t	Weight					1100	g
Size	Package box size					160 × 145 × 65	mm

PERFORMANCE CURVES FIGURE

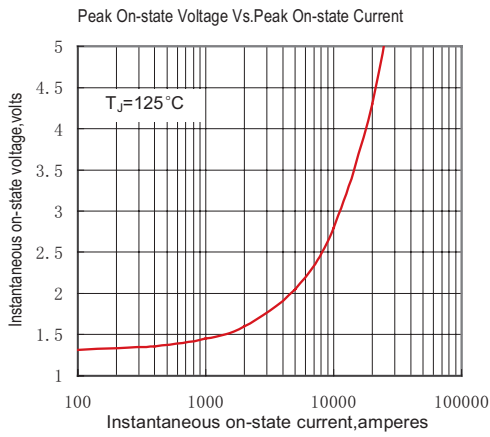


Fig.1

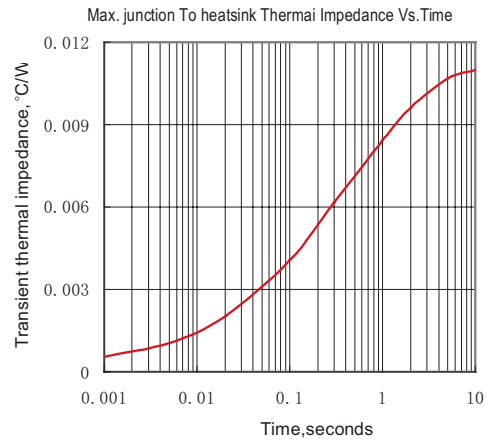


Fig.2

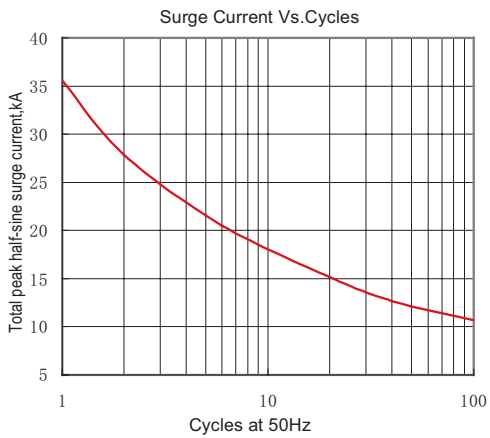


Fig.3

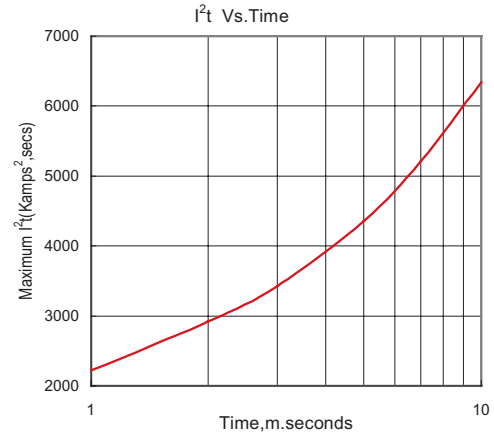


Fig.4

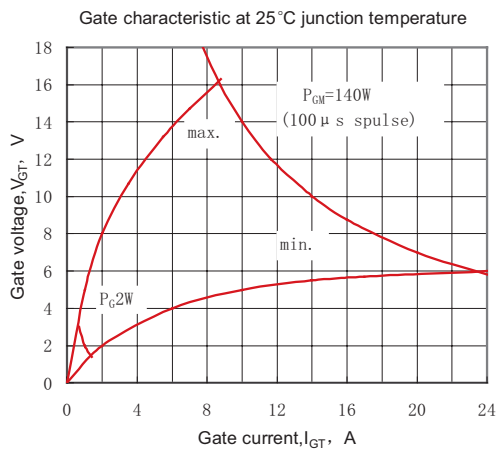


Fig.5

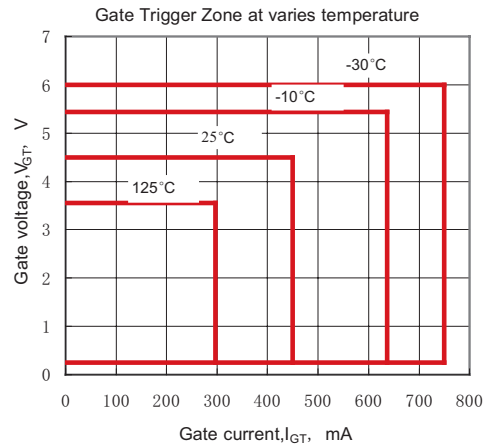
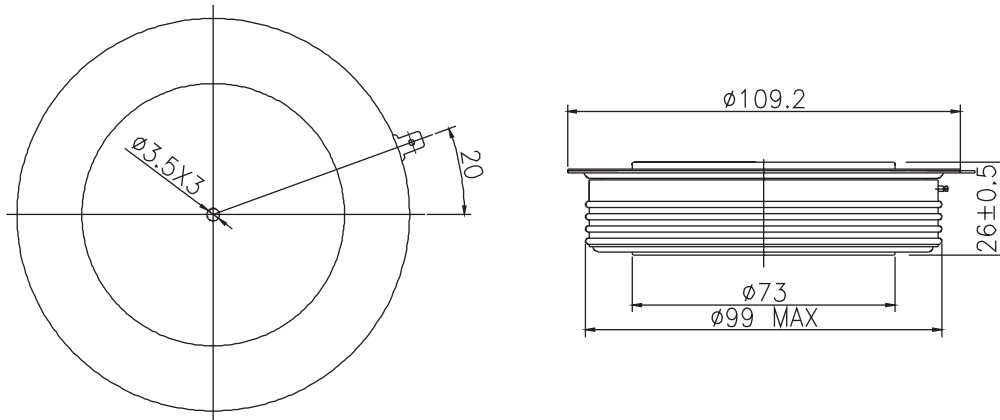


Fig.6

OUTLINE



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